

# 405nm Laser Diode

### **■** Features

Output Power: 20mW (CW)
Efficient Quantum Well Structure
Standard TO-18 Package



# ■ Absolute Maximum Ratings

(Tc=25°C)

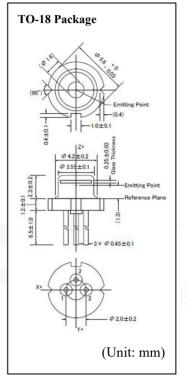
Item	Symbol	Absolute Maximum	Unit
		Ratings	
Optical Output Power	Po	25	mW
LD Reverse Voltage	Vr (LD)	2	V
Storage Temperature	Tstg	-40~85	°C
Operating Case Temperature	Тс	-10~80	°C

## ■ Initial Electrical/Optical Characteristics

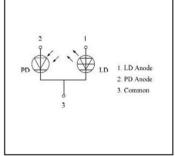
(Tc=25°C)

= Illitial Electrical Optical Characteristics			(10-23 0)
Item	Symbol	Тур.	Unit
Optical Output	Po	20	mW
Peak Wavelength*	λр	405±5	nm
Threshold Current	Ith	≤0.017	A
Operating Current	Iop	≤0.032	A
Slope Efficiency	η	≥1.2	W/A
Operating Voltage	Vop	≤4.5	V
Horizontal Beam Divergence	θ//	≤9	deg.
Vertical Beam Divergence	θ⊥	≤19	deg.
Polarization		TE	

#### **Outline Dimension**



## **Pin Connection**



All figures in this specification are measured by CNI's method and may contain measurement deviations.

The above specifications are for reference purpose only and subjected to change without prior notice.



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<sup>\*</sup> Measuring specifications.